

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if Known		
			Application Number		
			Filing Date		
			First Named Inventor	Dharmesh Jawarani	
			Group Art Unit		
			Examiner Name		
Sheet	1	of	2	Attorney Docket Number	SC13207TP

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number -Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ Number ⁴ Kind Code ² (if known)		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
✓	AA	WO 00/36634		06-22-2000	Bai et al.		

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
✓	AB	WIELUNSKI, L. et al.; "Alteration of Ni silicide formation by N implantation"; Applied Physics Letters; USA; 01-15-1981; pp 106-108; Vol. 38, No. 2; American Institute of Physics; USA.	
✓	AC	D'HEURLE, F. et al. ; "Diffusion in intermetallic compounds with the CaF ₂ structure: A marker study of the formation of NiSi ₂ thin films"; Journal of Applied Physics; August, 1982; pp 5678-5681; Vol. 53, No. 8; American Institute of Physics; USA.	
✓	AD	CHENG, L.W. et al.; "Effects of nitrogen ion implantation on the formation of nickel silicide contacts on shallow junctions"; Thin Solid Films; 1999; pp 412-416; Elsevier Science S.A..	

Examiner Signature	<i>N. H. M. M. M.</i>	Date Considered	01/26/06
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NON PATENT LITERATURE DOCUMENTS (cont.)							
V4	AE	LEE, P.S. et al.; "Improved NiSi Salicide Process using Presilicide N ₂ ⁺ Implant for MOSFETs"; IEEE Electron Device Letters; December, 2000; pp 566-568; IEEE.					
	AF	LEE, P.S. et al; "Nickel Silicide Formation on Si(100) and Poly-Si with a Presilicide N ₂ ⁺ Implantation"; Journal of Electronic Materials; 2001; pp 1554-1559; Vol. 30, No. 12; Electronic Materials; USA.					
	AG	CHAO, Tien-Sheng et al.; "Performance Improvement of Nickel Salicided n-Type Metal Oxide Semiconductor Field Effect Transistors by Nitrogen Implantation"; Jpn J. Appl Phys.; April 2002; pp L381-L383; Vol 41; The Japan Society of Applied Physics; Japan.					
	AH	LEE, P.S. et al; "Effect of Ion Implantation on Layer Inversion of Ni Silicided Polu-Si"; Journal of The Electrochemical Society; 2002; ppG505-509; The Electrochemical Society, Inc.					
	AI	CHOI, Chei-Jong et al; "Effects of Hydrogen Implantation on the Structural and Electrical Properties of Nickel Silicide"; Journal of The Electrochemical Society; 2002; pp G517-G521; The Electrochemical Society.					
	AJ	WONG, A.S.W. et al; "F-enhanced morphological and thermal stability of NiSi films on BF ₂ ⁺ -implanted Si(001); Applied Physics Letters; December 30, 2002; pp 5138-5140; Vol 81, No. 27; American Institute of Physics; USA.					
	AK	LAVOIE, C. et al.; "Towards implementation of a nickel silicide process for CMOS technologies"; Article in Press; 2003, pp 1-14; Elsevier B.V.					
	AL	OGHURO, T. et al.; "Nitrogen-doped Nickel Monosilicide Technique for Deep Submicron CMOS Salicide"; IEEE; 1995; pp 18.3.1-18.3.4.					
V4	AM	Related application 10/718,892 filed November 21, 2003					
<table border="1"> <tr> <td>Examiner Signature</td> <td><i>V. Y. [Signature]</i></td> <td>Date Considered</td> <td>01/26/06</td> </tr> </table>				Examiner Signature	<i>V. Y. [Signature]</i>	Date Considered	01/26/06
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